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[54] **ARTICLE COMPRISING α-HEXATHIENYL**

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[58] **Field of Search** 257/40, 66, 258, 257/347, 443, 64, 72; 252/510, 511

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[57] **ABSTRACT**

A previously unknown phase of α-hexathienyl, designated α-6T/HT, exhibits diffraction peaks at 2θ=4.31°, 8.64°, 12.96°, 17.32°, 26.15° and 29.08° in a CuK_α powder X-ray diffraction pattern, and is expected to have properties (e.g., high hole mobility) that make the phase desirable for use in, e.g., thin film transistors. Substitution of thin films of α-6T/HT for prior art organic thin films in thin film transistors and other devices is contemplated.

7 Claims, 2 Drawing Sheets